



INTEGRATED CIRCUIT

TECHNICAL DATA

TA7312P

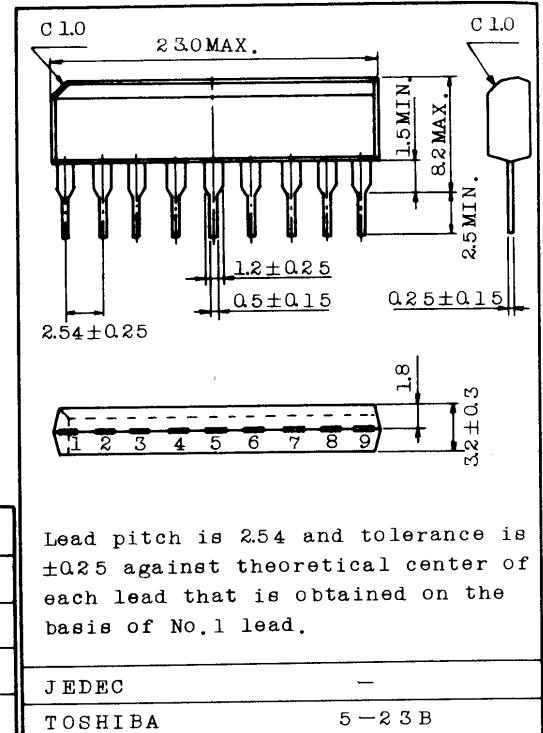
TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT

SILICON MONOLITHIC

Unit in mm

LOW NOISE DUAL PRE AMPLIFIER

- Low Noise : $V_{NI}=1.2\mu V_{rms}$ (Typ.)
- Excellent Cross Talk : C.T.=-65dB(Typ.)
- Wide Operating Supply Voltage Range : $V_{CC}=6\sim 15V$



MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	15	V
Power Dissipation (Note)	P_D	250	mW
Operating Temperature	T_{opr}	-30 ~ 75	°C
Storage Temperature	T_{stg}	-55 ~ 125	°C

(Note) Derated above $T_a=25^\circ C$ in the proportion of $5mW/^\circ C$.

ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, $V_{CC}=8V$, $R_L=10k\Omega$, $R_g=600\Omega$, $f=1kHz$, $T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Current	I_{CC}	-	$V_{IN}=0$	-	7.5	14	mA
Voltage Gain (Open Loop)	G_{VO}	-	$R_f=0$, $C_f=100\mu F$	62	70	-	dB
Maximum Output Voltage	V_{OM}	-	THD=0.5%	1.2	1.95	-	V_{rms}
Input Resistance	R_{IN}	-	-	-	50	-	$k\Omega$
Equivalent Input Noise Voltage	V_{NI}	-	$R_g=2.2k\Omega$, $BW=15\sim 30kHz$	-	1.2	2.7	μV_{rms}
Cross Talk	C.T.	-	$f=10kHz$, $R_g=2.2k\Omega$	-55	-65	-	dB